





20V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

DV	D Mov	I _D Max	
BV _{DSS}	R _{DS(ON)} Max	T _A = +25°C	
20V	0.99Ω @ V _{GS} = 4.5V	0.54A	
	1.2Ω @ V _G S = 2.5V	0.49A	
	1.8Ω @ V _{GS} = 1.8V	0.4A	
	2.4Ω @ V _G S = 1.5V	0.35A	

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low Package Profile
- 0.6mm x 0.4mm Package Footprint
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
 - For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

 https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: X2-DFN0604-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe; Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.001 grams (Approximate)

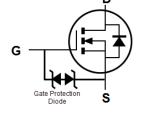












Top View Package Pin Configuration

Equivalent Circuit

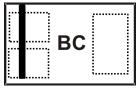
Ordering Information (Note 4)

Part Number	Case	Packaging	
DMN2991UFO-7B	X2-DFN0604-3	10k/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



BC= Product Type Marking Code Bar Denotes Gate and Source Side

Top View



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage	Vgss	±8	V		
Continuous Drain Current (Note 5) \/ 45\/	Steady	T _A = +25°C	- I _D	0.54	- A
Continuous Drain Current (Note 5) V _{GS} = 4.5V	State	T _A = +85°C		0.43	
Pulsed Drain Current (Note 6)			I _{DM}	1.2	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	Steady State	P _D	0.44	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Reja	281	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

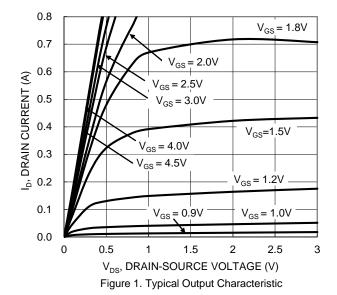
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	20	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	V _{DS} = 16V, V _{GS} = 0V	
Gate-Source Leakage	Igss	_	_	±10	μA	$V_{GS} = \pm 5V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	0.4	1	1.0	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
		l	0.5	0.99	Ω	$V_{GS} = 4.5V, I_{D} = 100mA$	
Static Drain-Source On-Resistance	Proyent		0.6	1.2		$V_{GS} = 2.5V, I_{D} = 50mA$	
Static Drain-Source On-Nesistance	RDS(ON)	_	0.8	1.8		$V_{GS} = 1.8V, I_D = 20mA$	
		_	1.0	2.4		$V_{GS} = 1.5V, I_D = 10mA$	
Diode Forward Voltage	VsD	_	0.7	1.0	V	V _G S = 0V, I _S = 150mA	
DYNAMIC CHARACTERISTICS (Note 8)					•		
Input Capacitance	Ciss	_	21.5	_	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	4.9	_	pF		
Reverse Transfer Capacitance	Crss	_	3.7	_	pF	1 – 1.000112	
Gate Resistance	Rg	_	0.94	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge	Qg	_	0.35	_	nC	V _{GS} = 4.5V, V _{DS} = 10V, -I _D = 250mA	
Gate-Source Charge	Qgs		0.07	_	nC		
Gate-Drain Charge	Qgd		0.08	_	nC		
Turn-On Delay Time	td(on)		5.6	_	ns	$\begin{aligned} &V_{DD}=10V,V_{GS}=4.5V,\\ &R_{L}=47\Omega,R_{g}=10\Omega,\\ &I_{D}=200mA \end{aligned}$	
Turn-On Rise Time	t _R		4.9	_	ns		
Turn-Off Delay Time	tD(OFF)	_	60.6	_	ns		
Turn-Off Fall Time	tF	_	27.6	_	ns		

Notes:

- Device mounted on FR-4 PCB, with minimum recommended pad layout.
 Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.





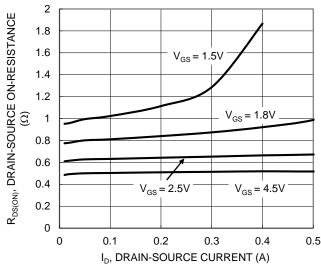


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

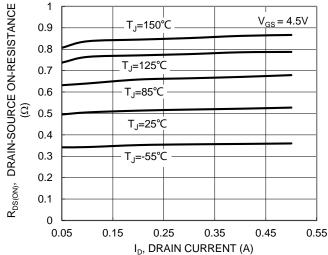


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

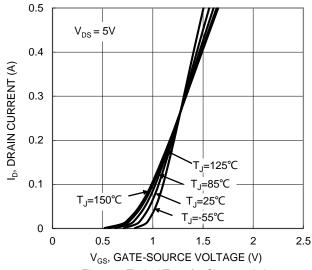


Figure 2. Typical Transfer Characteristic

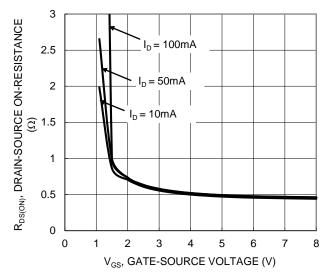


Figure 4. Typical Transfer Characteristic

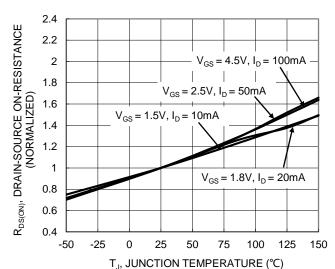


Figure 6. On-Resistance Variation with Junction Temperature



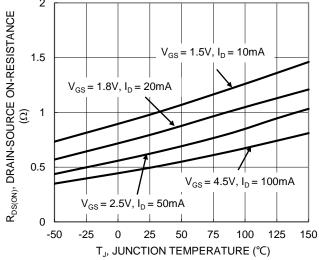
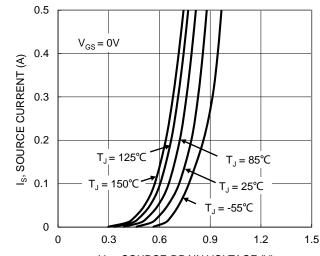


Figure 7. On-Resistance Variation with Junction Temperature



V_{SD}, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

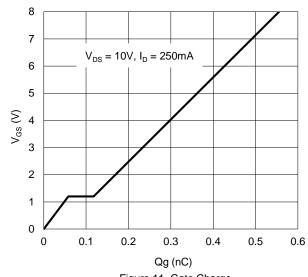


Figure 11. Gate Charge

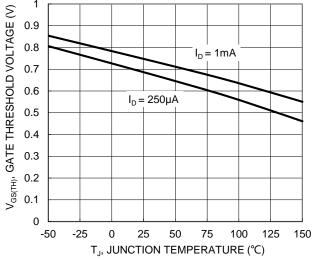
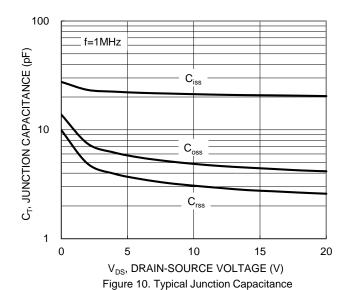


Figure 8. Gate Threshold Variation vs. Junction Temperature





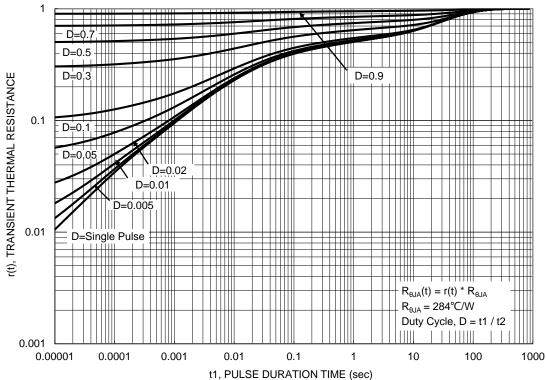


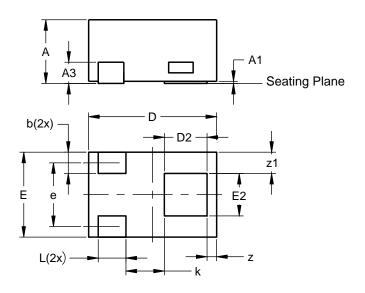
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3

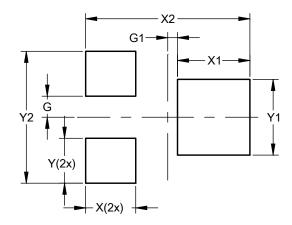


X2-DFN0604-3					
Dim	Min	Max	Тур		
Α		0.40	0.36		
A1	0.00	0.03	0.02		
A3			0.10		
b	0.07	0.15	0.10		
D	0.55	0.65	0.60		
D2	0.15	0.25	0.20		
Е	0.35	0.45	0.40		
E2	0.15	0.25	0.20		
e			0.30		
k	0.15				
L	0.10	0.18	0.13		
Z			0.045		
z1			0.10		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN0604-3



Dimensions	Value (in mm)
G	0.075
G1	0.035
Х	0.180
X1	0.260
X2	0.590
Y	0.160
Y1	0.270
Y2	0.470



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